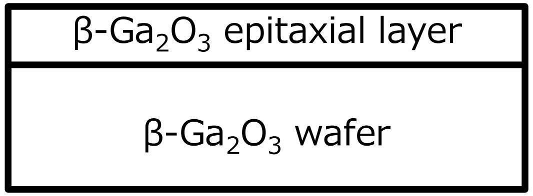
Standard specifications of 10×15 mm^2 β-Ga_2O_3 epitaxial wafer (by MBE)

Epitaxial layer

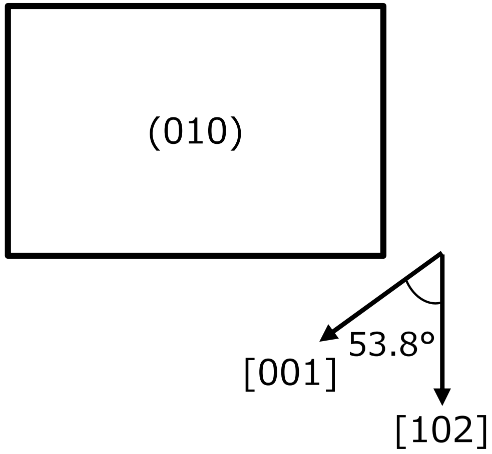
Items	Specifications	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration *A value can be selected within the described range.	Specify a value in the range between 1×10^{17} and 2×10^{18} cm^{-3}	-
Thickness *A value can be selected within the described range.	Specify a value in the range between 0.1 and 0.5 μm	



Cross section of β-Ga_2O_3 epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration	Using the range of 1 ～ 9×10^{18} cm^{-3}	-
Resistivity	-	≧10^{10} Ωcm
Orientation	(010)	
Size	10×15 mm^2	
Thickness	0.5 mm	
XRD FWHM	≦150 arcsec	
Off set angle	0°±1°	



Orientation

Remarks
1 These products must be used for research and development purposes only.
2 The substrates must not be used as a seed crystal.
3 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.
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